

FQP12P20 Information

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Part Number FQP12P20

ManufacturerFairchild/ON SemiconductorCategoryDiscrete Semiconductor ProductsTransistors - FETs, MOSFETs - Single

Description MOSFET P-CH 200V 11.5A TO-220

Package TO-220-3

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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FQP12P20 Specifications

Manufacturer Part Number FQP12P20 Manufacturer Fairchild/ON Semiconductor Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package TO-220-3 Series QFET? FET Type P-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 200V Current - Continuous Drain (Id) @ 25°C 11.5A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 5V @ 250µA Gate Charge (Qg) (Max) @ Vgs 40nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 1200pF @ 25V Vgs (Max) ±30V FET Feature - Power Dissipation (Max) 120W (Tc) Rds On (Max) @ Id, Vgs 470 mOhm @ 5.75A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220-3 Package / Case TO-220-3		
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Series QFET? FET Type P-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 200V Current - Continuous Drain (Id) @ 25°C 11.5A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 5V @ 250μA Gate Charge (Qg) (Max) @ Vgs 40nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 1200pF @ 25V Vgs (Max) ±30V FET Feature - Power Dissipation (Max) 120W (Tc) Rds On (Max) @ Id, Vgs 470 mOhm @ 5.75A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220-3 Package / Case TO-220-3		Transistors - FETs, MOSFETs - Single
FET TypeP-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)200VCurrent - Continuous Drain (Id) @ 25°C11.5A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id5V @ 250μAGate Charge (Qg) (Max) @ Vgs40nC @ 10VInput Capacitance (Ciss) (Max) @ Vds1200pF @ 25VVgs (Max)±30VFET Feature-Power Dissipation (Max)120W (Tc)Rds On (Max) @ Id, Vgs470 mOhm @ 5.75A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220-3Package / CaseTO-220-3	Package	TO-220-3
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Drain to Source Voltage (Vdss)200VCurrent - Continuous Drain (Id) @ 25°C11.5A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id5V @ 250μAGate Charge (Qg) (Max) @ Vgs40nC @ 10VInput Capacitance (Ciss) (Max) @ Vds1200pF @ 25VVgs (Max)±30VFET Feature-Power Dissipation (Max)120W (Tc)Rds On (Max) @ Id, Vgs470 mOhm @ 5.75A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220-3Package / CaseTO-220-3	FET Type	P-Channel
Current - Continuous Drain (Id) @ 25°C11.5A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id5V @ 250μAGate Charge (Qg) (Max) @ Vgs40nC @ 10VInput Capacitance (Ciss) (Max) @ Vds1200pF @ 25VVgs (Max)±30VFET Feature-Power Dissipation (Max)120W (Tc)Rds On (Max) @ Id, Vgs470 mOhm @ 5.75A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220-3Package / CaseTO-220-3	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id5V @ 250μAGate Charge (Qg) (Max) @ Vgs40nC @ 10VInput Capacitance (Ciss) (Max) @ Vds1200pF @ 25VVgs (Max)±30VFET Feature-Power Dissipation (Max)120W (Tc)Rds On (Max) @ Id, Vgs470 mOhm @ 5.75A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220-3Package / CaseTO-220-3	Drain to Source Voltage (Vdss)	200V
Vgs(th) (Max) @ Id 5V @ 250μA Gate Charge (Qg) (Max) @ Vgs 40nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 1200pF @ 25V Vgs (Max) ±30V FET Feature - Power Dissipation (Max) 120W (Tc) Rds On (Max) @ Id, Vgs 470 mOhm @ 5.75A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220-3 Package / Case TO-220-3	Current - Continuous Drain (Id) @ 25°C	11.5A (Tc)
Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds 1200pF @ 25V Vgs (Max) ET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 470 mOhm @ 5.75A, 10V Operating Temperature Jenus Andrew Company Through Hole Supplier Device Package TO-220-3 Package / Case TO-220-3	Drive Voltage (Max Rds On, Min Rds On)	10V
Input Capacitance (Ciss) (Max) @ Vds 1200pF @ 25V Vgs (Max) ET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 470 mOhm @ 5.75A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220-3 Package / Case TO-220-3	Vgs(th) (Max) @ Id	5V @ 250μA
Vgs (Max)±30VFET Feature-Power Dissipation (Max)120W (Tc)Rds On (Max) @ Id, Vgs470 mOhm @ 5.75A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220-3Package / CaseTO-220-3	Gate Charge (Qg) (Max) @ Vgs	40nC @ 10V
FET Feature - 120W (Tc) Rds On (Max) @ Id, Vgs 470 mOhm @ 5.75A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220-3 Package / Case TO-220-3	Input Capacitance (Ciss) (Max) @ Vds	1200pF @ 25V
Power Dissipation (Max) Rds On (Max) @ Id, Vgs 470 mOhm @ 5.75A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220-3 Package / Case TO-220-3	Vgs (Max)	±30V
Rds On (Max) @ Id, Vgs470 mOhm @ 5.75A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220-3Package / CaseTO-220-3	FET Feature	-
Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220-3 Package / Case TO-220-3	Power Dissipation (Max)	120W (Tc)
Mounting Type Through Hole Supplier Device Package TO-220-3 Package / Case TO-220-3	Rds On (Max) @ Id, Vgs	470 mOhm @ 5.75A, 10V
Supplier Device Package TO-220-3 Package / Case TO-220-3	Operating Temperature	-55°C ~ 150°C (TJ)
Package / Case TO-220-3	Mounting Type	Through Hole
	Supplier Device Package	TO-220-3
Report errors?	Package / Case	TO-220-3
		Report errors?

FQP12P20 Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

FQP12P20 Payment Methods





















FQP12P20 Shipping Methods













If you have any question about FQP12P20, please do not hesitate to contact us!

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